

# isc N-Channel MOSFET Transistor

## TK12J60U

RDS(d • Enhanc Vth = • 100% a • Minimu perform • DESCR • Switchin	ain-source on-resistance: on) $\leq 0.4 \Omega$ . cement mode: 3.0 to $5.0V$ (V <sub>DS</sub> = 10 V, I <sub>D</sub> =1mA) avalanche tested m Lot-to-Lot variations for robust de nance and reliable operation	I 2 3 0   I 2 3 0 0   I 2 3 0 0   I 2 3 0 0   I 2 3 0 0   I 2 3 0 0   I 2 3 0 0   I 2 3 0 0   I 2 3 0 0   I 2 3 0 0   I 2 3 0 0   I 2 3 0 0   I 2 3 0 0   I 3 0 0 0   I 3 0 0 0   I 1 3 0 0 0   I 1 2 0 0 0 0   I 1 2 3 0 0 0 0   I 1 2 3		
SYMBOL	PARAMETER	VALUE	UNIT	
VDSS	Drain-Source Voltage	600	V	
$V_{GS}$	Gate-Source Voltage	±30	V	κ <sup>†</sup> G → ←L
ID	Drain Current-Continuous	12	A	<u>↓</u> ∪ ∪ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓
I <sub>DM</sub>	Drain Current-Single Pulsed	24	А	→ ← R ← N →
P <sub>D</sub>	Total Dissipation @T <sub>C</sub> =25℃	144	W	DIM MIN MAX A 19.60 20.30 B 15.50 15.70
Tj	Max. Operating Junction Temperature	150	°C	C   4.70   4.90     D   0.90   1.10     E   1.90   2.10     F   3.40   3.60
T <sub>stg</sub>	Storage Temperature	-55~150	°C	G 2.90 3.20 H 3.20 3.40 J 0.595 0.605
THERMAL CHARACTERISTICS				K 19.80 20.70 L 1.90 2.20 N 10.89 10.91
SYMBOL	PARAMETER	MAX	UNIT	Q 4.90 5.10 R 3.35 3.45 S 1.995 2.100
Rth(ch-c)	Channel-to-case thermal resistance	0.868	°C/W	U 5.90 6.20 Y 9.90 10.10



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#### **ELECTRICAL CHARACTERISTICS**

#### $T_{\rm C}\text{=}25^\circ\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> =10mA	600			V
V <sub>GS</sub> (th)	Gate Threshold Voltage	V <sub>DS</sub> =10V; I <sub>D</sub> =1mA	3.0		5.0	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =6A			0.4	Ω
lgss	Gate-Source Leakage Current	V <sub>GS</sub> = ±30V;V <sub>DS</sub> = 0V			±1	μA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =600V; V <sub>GS</sub> = 0V			100	μA
V <sub>SDF</sub>	Diode forward voltage	I <sub>DR</sub> =12A, V <sub>GS</sub> = 0 V			1.7	V

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